

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

There is provided a technique that includes: (a) loading a substrate into a process container at a loading temperature; (b) setting an interior of the process container to a film formation temperature; (c) forming a metal film on a surface of the substrate by supplying a process gas into the process container; (d) setting the interior of the process container to an unloading temperature lower than the loading temperature; and (e) unloading the substrate from the process container.

Fig. 3